

8. The electroluminescent device of claim 1, wherein said reflecting structure comprises a layer of Al.

5 9. The electroluminescent device of any of claims 1 to 8, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.

10 10. The electroluminescent device of any of claims 1 to 8, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.

11. The electroluminescent device of claim 10, wherein said substrate is one of either clear plastic or glass.

15 12. The electroluminescent device of claim 1, wherein said intermediate layers include one of either light emitting polymers or inorganic light emitting materials.

20 13. The electroluminescent device of claim 7, wherein said semi-reflecting structure comprises AlSiO(ratio 3:2, 5.5 nm), SiO<sub>2</sub> (60 nm), and aluminum (10 nm).

14. The electroluminescent device of claim 6, wherein said thicknesses of the intermediate layers are as follows: AlQ<sub>3</sub> = 600 Å, TPD = 450 Å, CuPC = 250 Å, ITO = 1200 Å.

## AMENDED CLAIMS

received by the International Bureau on 02 November 2004 (02.11.04) : claims 1 to 14 are unchanged and new claims 15 and 16 have been added.

8. The electroluminescent device of claim 1, wherein said reflecting structure comprises a layer of Al.

5 9. The electroluminescent device of any of claims 1 to 8, wherein said reflecting structure is deposited on a substrate so as to form a top emission device.

10 10. The electroluminescent device of any of claims 1 to 8, wherein said semi-reflecting structure is deposited on a transparent substrate so as to form a bottom emission device.

11. The electroluminescent device of claim 10, wherein said substrate is one of either clear plastic or glass.

15 12. The electroluminescent device of claim 1, wherein said intermediate layers include one of either light emitting polymers or inorganic light emitting materials.

20 13. The electroluminescent device of claim 7, wherein said semi-reflecting structure comprises AlSiO(ratio 3:2, 5.5 nm), SiO<sub>2</sub> (60 nm), and aluminum (10 nm).

24 14. The electroluminescent device of claim 6, wherein said thicknesses of the intermediate layers are as follows: AlQ<sub>3</sub> = 600 Å, TPD = 450 Å, CuPC = 250 Å, ITO = 1200 Å.

25 15. The electroluminescent device of claim 1, wherein said intermediate layers are selected such that the 360° phase change extends over the visible light range.

30 16. The electroluminescent device of claim 1, wherein the layers are selected to have a refractive index that increases with wavelength.

**STATEMENT UNDER ARTICLE 19 (1)**

New claims 15 and 16 have been added to further define the present invention. It is believed that these claims are fully supported by the disclosure as originally filed at, for example, page 11.